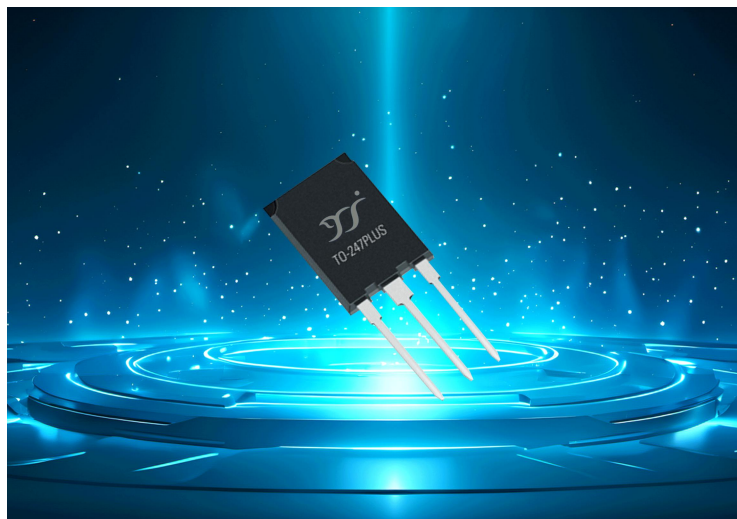


新品发布

用于光伏逆变器、储能逆变器的微沟槽IGBT

Micro-pattern trenches IGBT for photovoltaic inverter & energy storage inverter



产品介绍

扬杰科技近日推出了新一代 TO-247PLUS 封装 160A 650V IGBT单管，产品采用1.6um微沟槽工艺平台，大大提高功率密度，具有较低的导通损耗及开关损耗，为光伏储能行业提供大功率单管解决方案。

新品发布

1. 采用1.6um微沟槽工艺平台；
2. 电压等级为650V，电流等级为160A@Tc=100°C；
3. 低导通损耗，低开关损耗；
4. 配置有软度极佳的反并联快恢复二极管

产品规格书详见官网

Product Name	V_{CES} (V)	I_C (A)	$V_{GE(th)}$ (V)	$V_{CE(sat)}$ (V)	V_F (V)	P_d (W)	T_j (°C)
DGQ160N65CTS2A	650	160	4.0	1.55	2.1	714	-40~175

产品特点



光伏逆变器

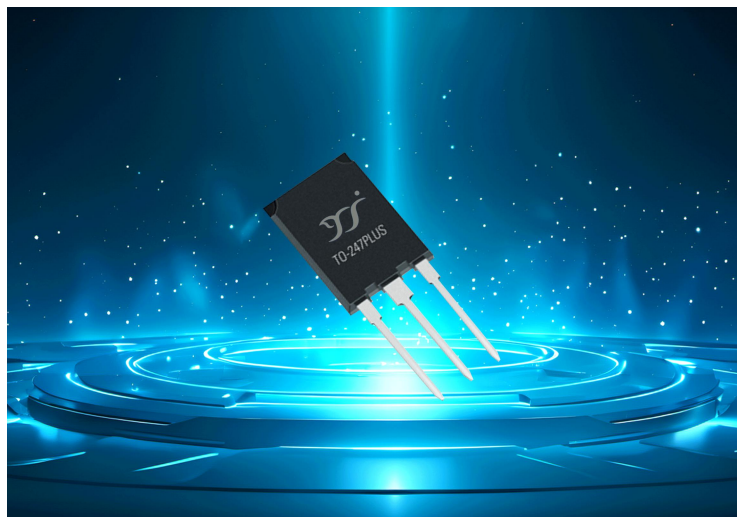


储能逆变器

典型应用

NEW
PRODUCT

Micro-pattern Trenches IGBT for Photovoltaic Inverter & Energy Storage Inverter



Product Introduction

Yangjie Technology recently launched a new generation of TO-247PLUS packaged 160A 650V discrete IGBT. The product adopts 1.6um micro-pattern trenches process platform, greatly improving power density, having low conduction and switching loss. It provides high-power discrete IGBT solutions for the photovoltaic inverter and energy storage inverter.

New Product Announcement

1. Adopting 1.6um micro-pattern trenches process platform;
2. 650V breakdown voltage, $I_c=160A@T_c=100^{\circ}C$;
3. Low conduction loss, low switching loss;
4. Copacked with Very soft, fast recovery antiparallel diode;

Product
Features

Please refer to the official website for more details

Product Name	V_{CES} (V)	I_c (A)	$V_{GE(th)}$ (V)	$V_{CE(sat)}$ (V)	V_F (V)	P_d (W)	T_j ($^{\circ}C$)
DGQ160N65CTS2A	650	160	4.0	1.55	2.1	714	-40~175



Photovoltaic inverter



Energy storage inverter

Typical
Applica-
-tions